



EMH2801

P-Channel Power MOSFET -20V, -3A, 85mΩ, Single EMH8 with Schottky Diode

ON Semiconductor®

<http://onsemi.com>

Features

- Composite type with a P-Channel Silicon MOSFET and a Schottky Barrier Diode contained in one package facilitating high-density mounting
- [MOSFET] • Low ON-resistance
- [SBD] • Small switching noise
- Halogen free compliance
- 1.8V drive
- Low forward voltage ($I_F=2.0A$, $V_F \text{ max}=0.46V$)

Specifications

Absolute Maximum Ratings at $T_a=25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings	Unit
[MOSFET]				
Drain-to-Source Voltage	V_{DS}		-20	V
Gate-to-Source Voltage	V_{GS}		± 10	V
Drain Current (DC)	I_D		-3	A
Drain Current (Pulse)	I_{DP}	$PW \leq 10\mu s$, duty cycle $\leq 1\%$	-20	A
Allowable Power Dissipation	P_D	When mounted on ceramic substrate (900mm ² ×0.8mm) 1unit	1.0	W
Channel Temperature	T_{ch}		150	°C
Storage Temperature	T_{stg}		-55 to +125	°C

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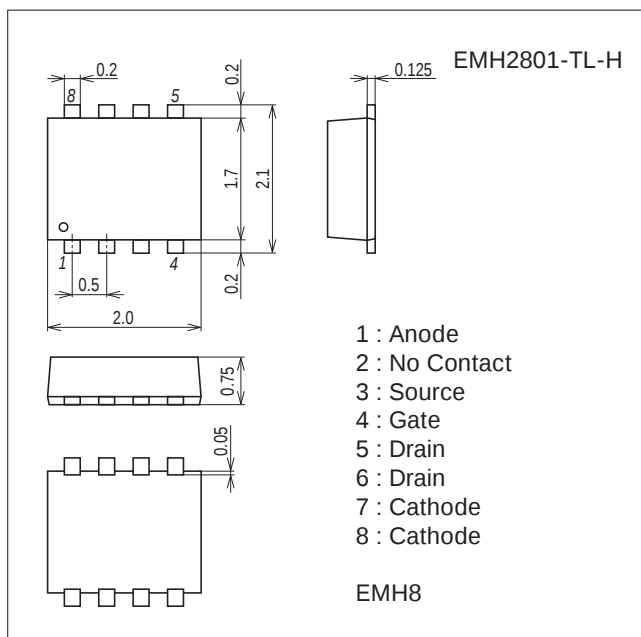
This product is designed to "ESD immunity < 200V**", so please take care when handling.

* Machine Model

Package Dimensions

unit : mm (typ)

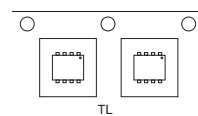
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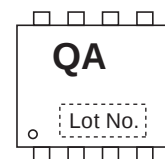
Product & Package Information

- Package : EMH8
- JEITA, JEDEC : -
- Minimum Packing Quantity : 3,000 pcs./reel

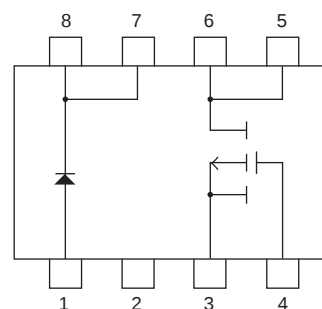
Packing Type : TL



Marking



Electrical Connection



EMH2801

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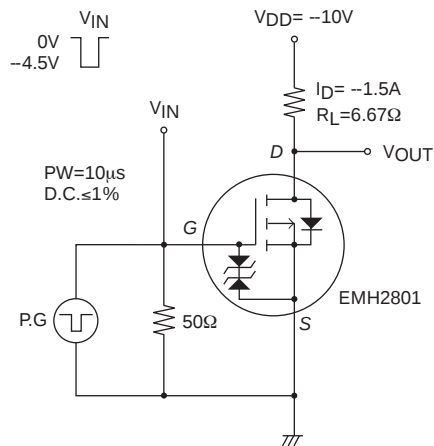
Parameter	Symbol	Conditions	Ratings	Unit
[SBD]				
Repetitive Peak Reverse Voltage	V_{RRM}		15	V
Nonrepetitive Peak Reverse Surge Voltage	V_{RSM}		15	V
Average Output Current	I_O	Rectangular wave	2.0	A
Surge Forward Current	I_{FSM}	50Hz sine wave, 1 cycle	20	A
Junction Temperature	T_J		-55 to +125	°C
Storage Temperature	T_{stg}		-55 to +125	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

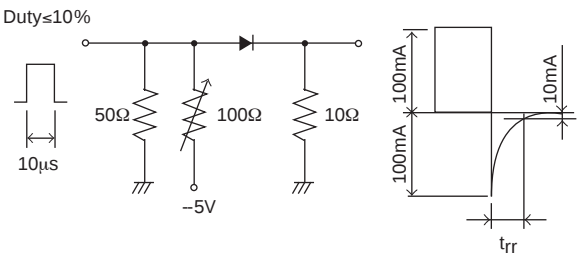
Electrical Characteristics at $T_a=25^{\circ}\text{C}$

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
[MOSFET]						
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=-1mA, VGS=0V	-20			V
Zero-Gate Voltage Drain Current	IDSS	VDS=-20V, VGS=0V			-1	μA
Gate-to-Source Leakage Current	IGSS	VGS=±8V, VDS=0V			±10	μA
Cutoff Voltage	VGS(off)	VDS=-10V, ID=-1mA	-0.4		-1.3	V
Forward Transfer Admittance	yfs	VDS=-10V, ID=-1.5A		3.6		S
Static Drain-to-Source On-State Resistance	RDS(on)1	ID=-1.5A, VGS=-4.5V		65	85	mΩ
	RDS(on)2	ID=-1A, VGS=-2.5V		98	137	mΩ
	RDS(on)3	ID=-0.5A, VGS=-1.8V		155	235	mΩ
Input Capacitance	Ciss	VDS=-10V, f=1MHz		320		pF
Output Capacitance	Coss			66		pF
Reverse Transfer Capacitance	Crss			50		pF
Turn-ON Delay Time	tD(on)	See specified Test Circuit.		7.1		ns
Rise Time	tr			21		ns
Turn-OFF Delay Time	tD(off)			37		ns
Fall Time	tf			32		ns
Total Gate Charge	Qg	VDS=-10V, VGS=-4.5V, ID=-3A		4.0		nC
Gate-to-Source Charge	Qgs			0.6		nC
Gate-to-Drain “Miller” Charge	Qgd			1.1		nC
Diode Forward Voltage	VSD	IS=-3A, VGS=0V		-0.83	-1.2	V
[SBD]						
Reverse Voltage	VR	IR=1mA	15			V
Forward Voltage	VF1	IF=1.0A		0.33	0.39	V
	VF2	IF=2.0A		0.39	0.46	V
Reverse Current	IR	VR=7.5V			300	μA
Interterminal Capacitance	C	VR=10V, f=1MHz		35		pF

Switching Time Test Circuit
(MOSFET)

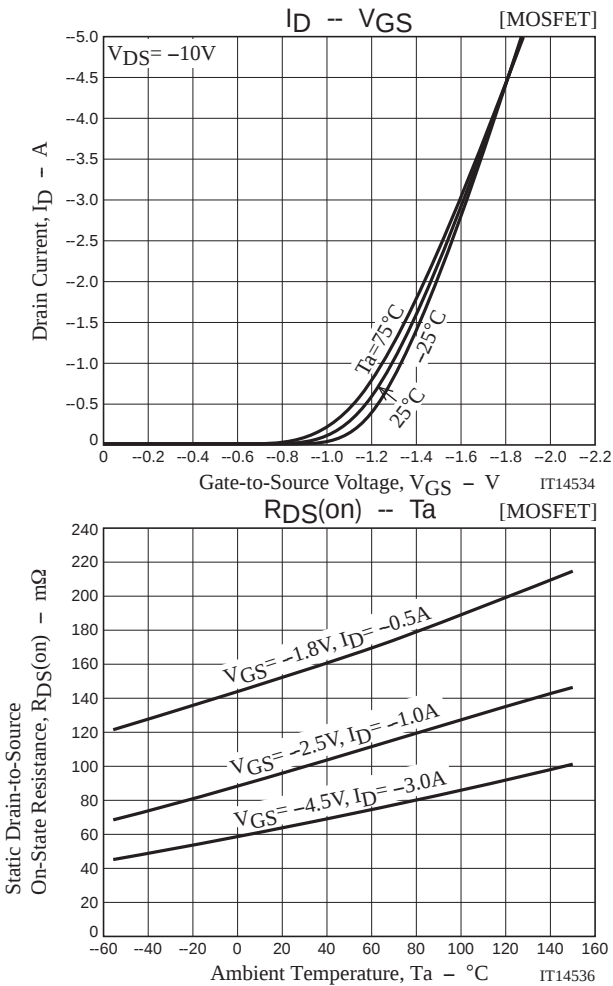
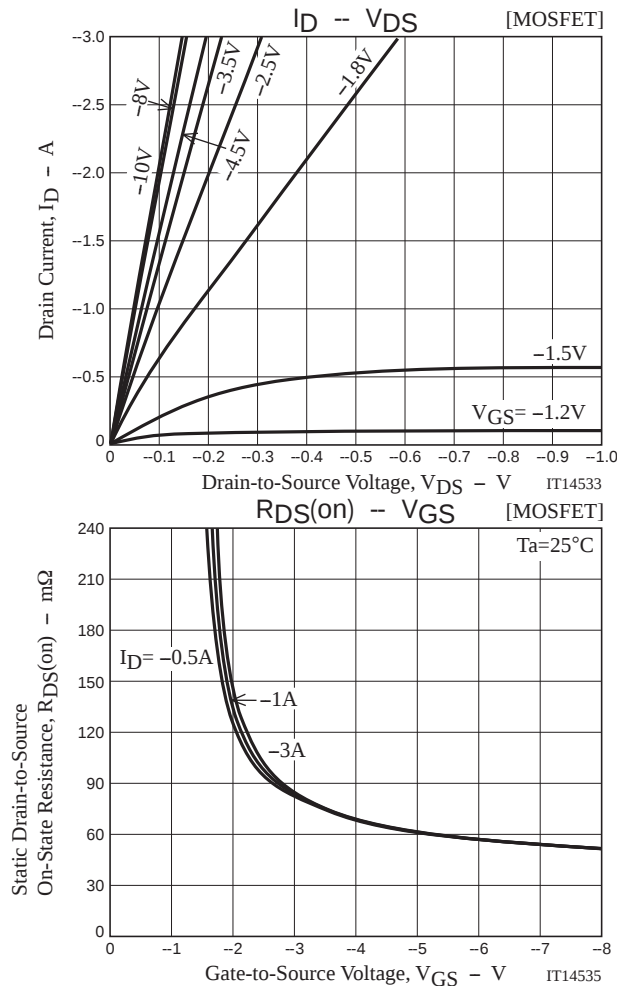


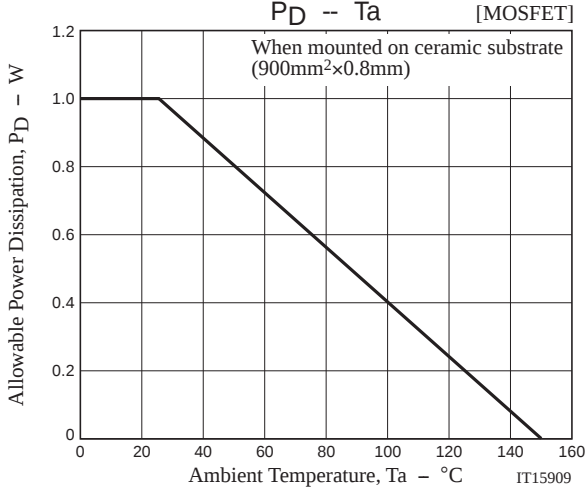
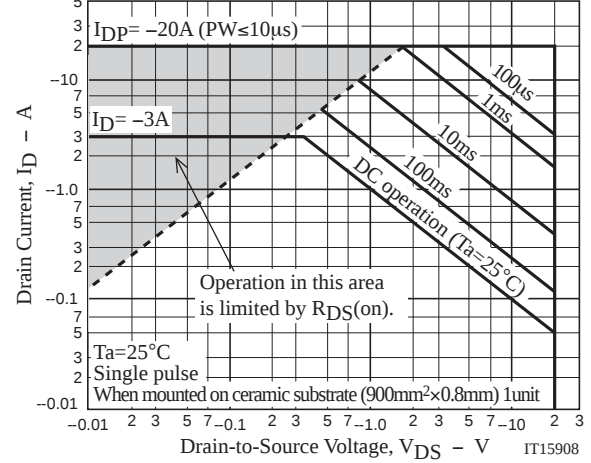
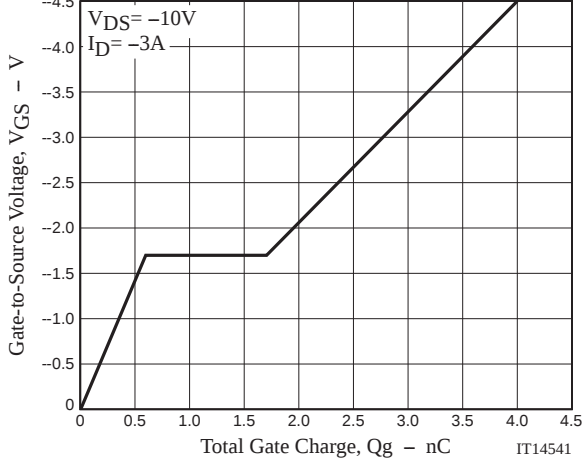
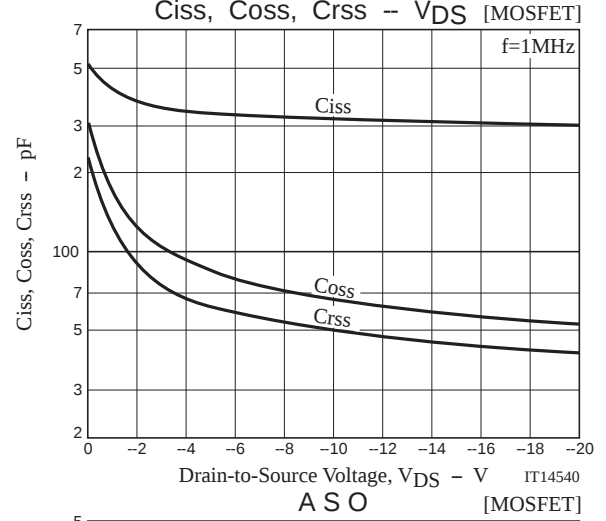
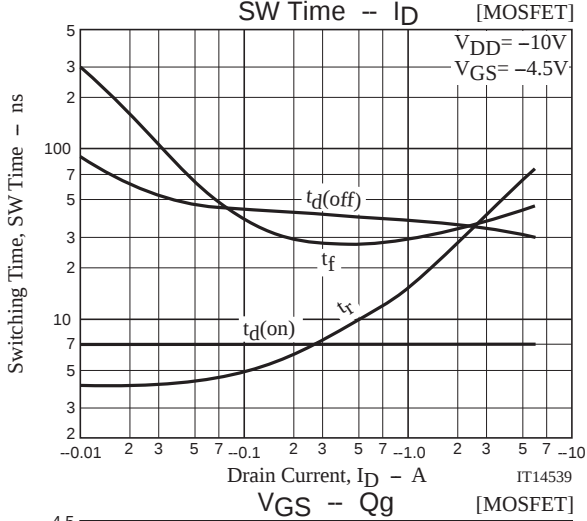
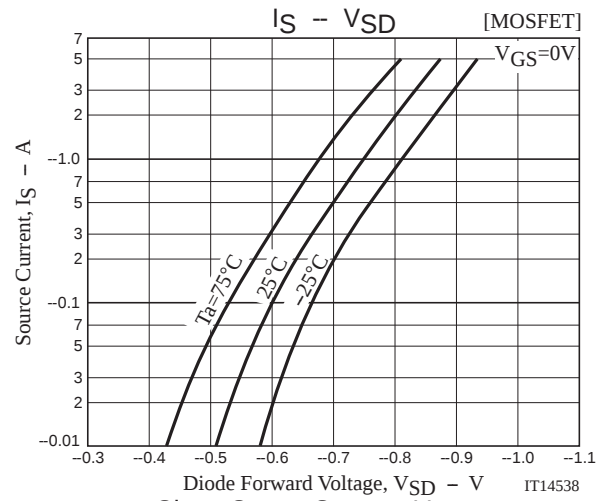
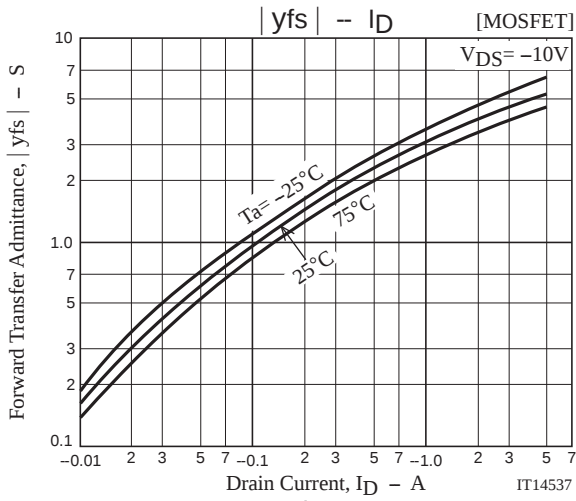
t_{rr} Test Circuit
(SBD)

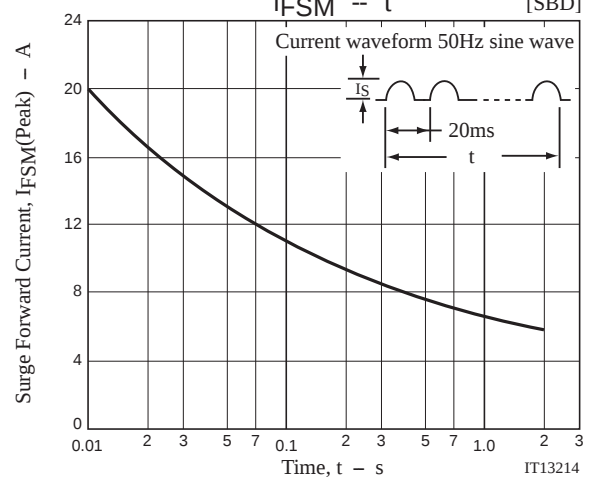
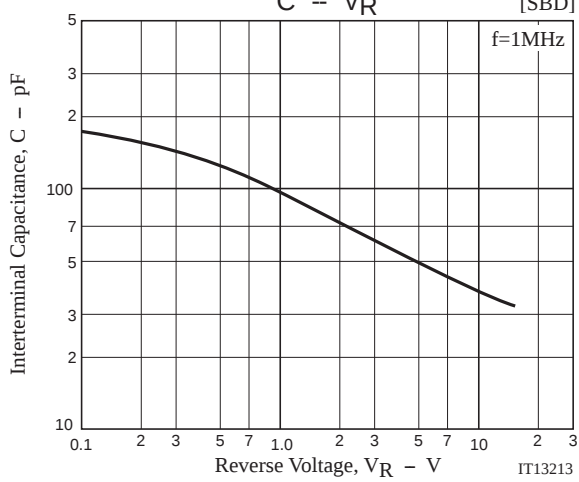
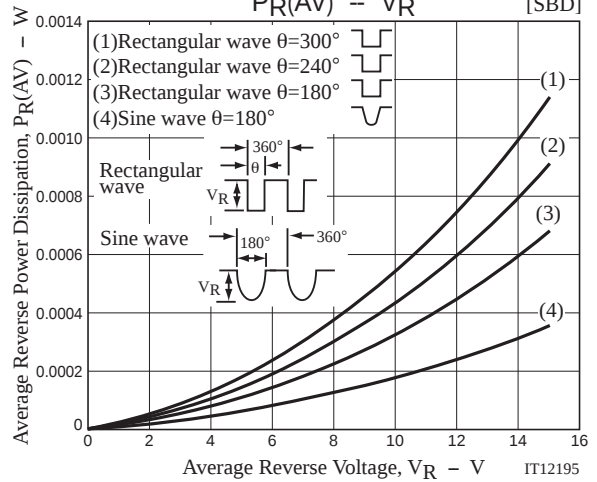
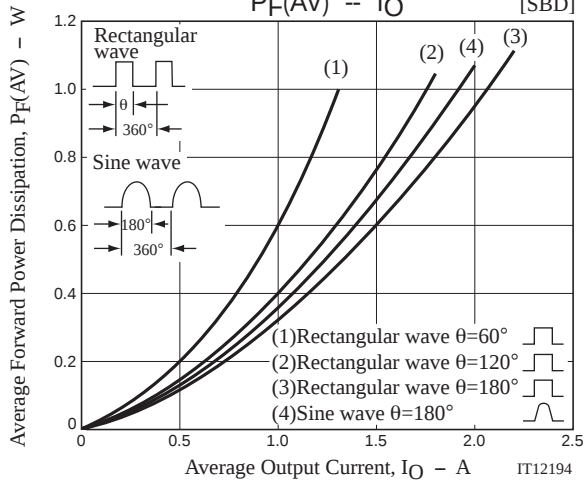
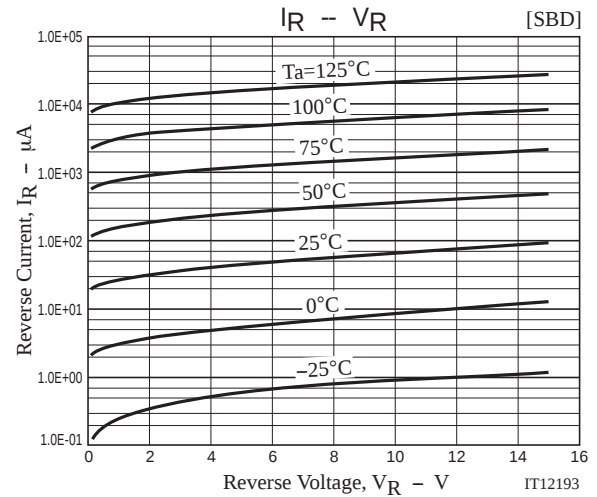
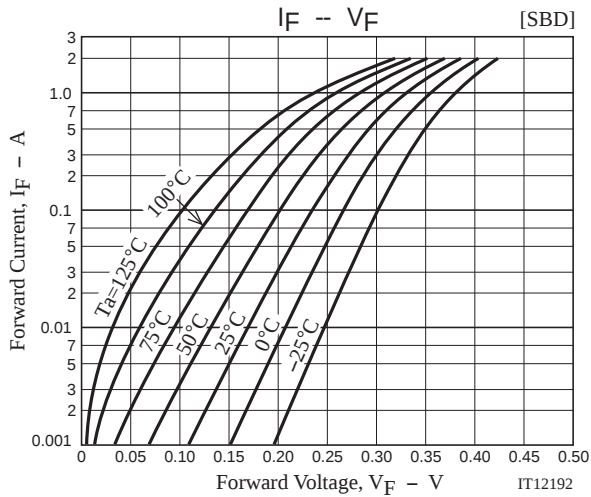


Ordering Information

Device	Package	Shipping	memo
EMH2801-TL-H	EMH8	3,000pcs./reel	Pb Free and Halogen Free







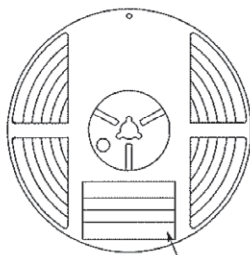
Embossed Taping Specification

EMH2801-TL-H

1. Packing Format

Package Name	Carrier Tape Type	Maximum Number of devices contained (pcs)			Packing format	
		Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)
EMH8	MCP4	3,000	15,000	90,000	5 reels contained Dimensions:mm (external) 183×72×185	6 inner boxes contained Dimensions:mm (external) 440×195×210

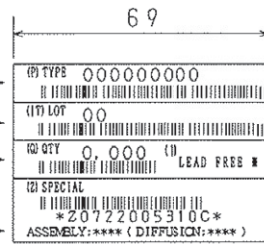
Packing method



Type No.
LOT No.
Quantity
Origin

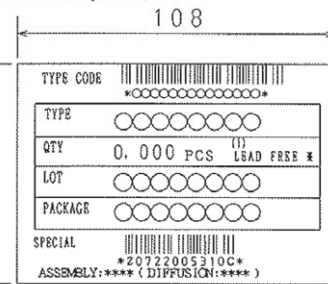
Reel label

Reel label, Inner box label
(unit:mm)



Outer box label

It is a label at the time of factory shipments.
The form of a label may change in physical distribution process.



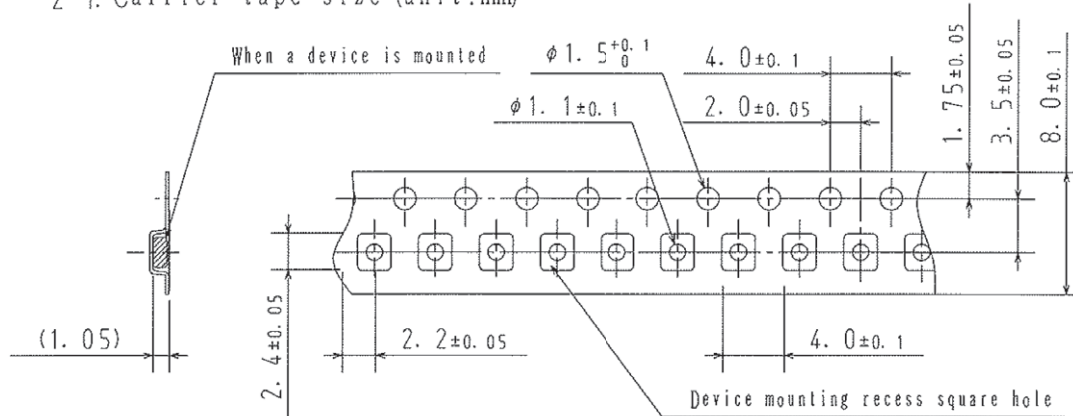
NOTE (1)

The LEAD FREE * description shows that the surface treatment of the terminal is lead free.

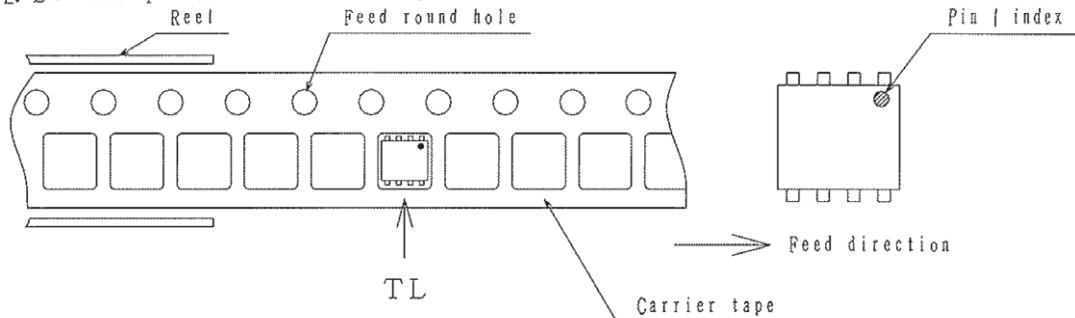
Label	JEITA Phase
LEAD FREE 3	JEITA Phase 3A
LEAD FREE 4	JEITA Phase 3

2. Taping configuration

2-1. Carrier tape size (unit:mm)

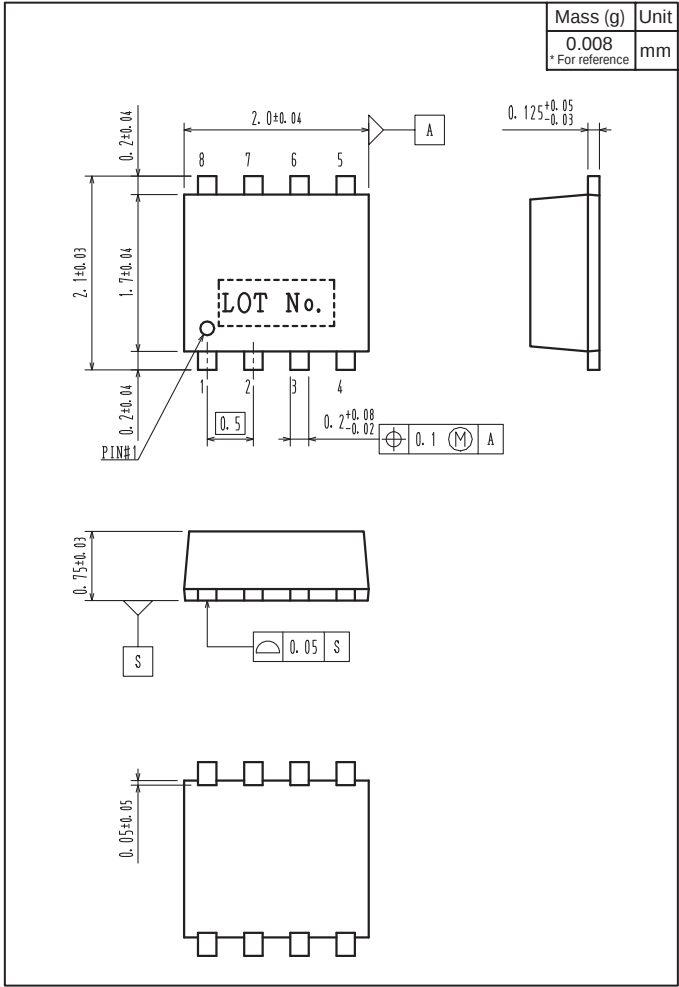


2-2. Device placement direction

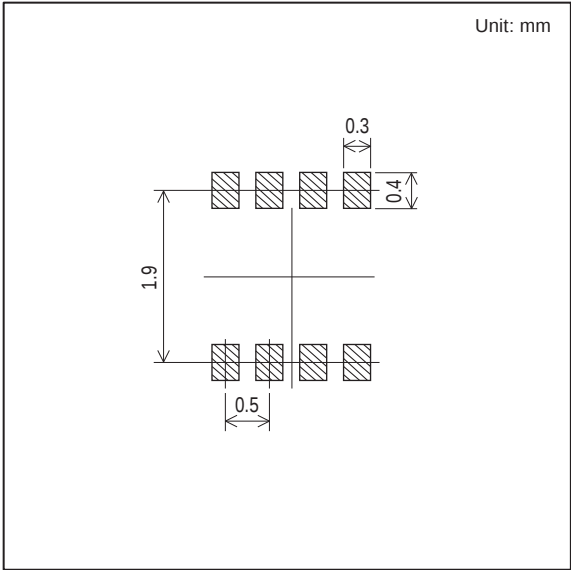


Those with pin 1 index on the feed hole side.....TL

Outline Drawing
EMH2801-TL-H



Land Pattern Example



Note on usage : Since the EMH2801 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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